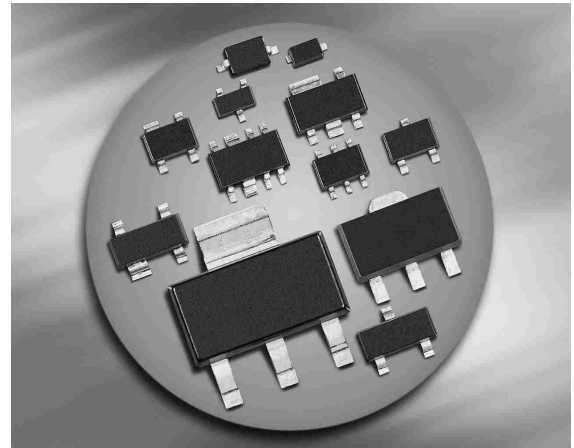


NPN Silicon AF Transistors

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 Hz and 15 kHz
- Complementary types:
BC857...-BC860...(PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101¹⁾



¹⁾BC847BL3 is not qualified according AEC Q101

Type	Marking	Pin Configuration						Package
BC847A	1Es	1=B	2=E	3=C	-	-	-	SOT23
BC847B	1Fs	1=B	2=E	3=C	-	-	-	SOT23
BC847BL3*	1F	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC847BW	1Fs	1=B	2=E	3=C	-	-	-	SOT323
BC847C	1Gs	1=B	2=E	3=C	-	-	-	SOT23
BC847CW	1Gs	1=B	2=E	3=C	-	-	-	SOT323
BC848A	1Js	1=B	2=E	3=C	-	-	-	SOT23
BC848B	1Ks	1=B	2=E	3=C	-	-	-	SOT23
BC848BL3	1K	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC848BW	1Ks	1=B	2=E	3=C	-	-	-	SOT323
BC848C	1Ls	1=B	2=E	3=C	-	-	-	SOT23
BC848CW	1Ls	1=B	2=E	3=C	-	-	-	SOT323
BC849B	2Bs	1=B	2=E	3=C	-	-	-	SOT23
BC849C	2Cs	1=B	2=E	3=C	-	-	-	SOT23
BC849CW	2Cs	1=B	2=E	3=C	-	-	-	SOT323
BC850B	2Fs	1=B	2=E	3=C	-	-	-	SOT23
BC850BW	2Fs	1=B	2=E	3=C	-	-	-	SOT323
BC850C	2Gs	1=B	2=E	3=C	-	-	-	SOT23
BC850CW	2Gs	1=B	2=E	3=C	-	-	-	SOT323

* Not qualified according AEC Q101

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage BC847..., BC850... BC848..., BC849...	V_{CEO}	45 30	V
Collector-emitter voltage BC847..., BC850... BC848..., BC849...	V_{CES}	50 30	
Collector-base voltage BC847..., BC850... BC848..., BC849...	V_{CBO}	50 30	
Emitter-base voltage BC847..., BC850... BC848..., BC849...	V_{EBO}	6 6	
Collector current	I_C	100	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	200	
Total power dissipation- $T_S \leq 71$ °C, BC847-BC850 $T_S \leq 135$ °C, BC847BL3-BC848BL3 $T_S \leq 124$ °C, BC847W-BC850W	P_{tot}	330 250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BC847-BC850 BC847BL3-BC848BL3 BC847W-BC850W	R_{thJS}	≤ 240 ≤ 60 ≤ 105	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

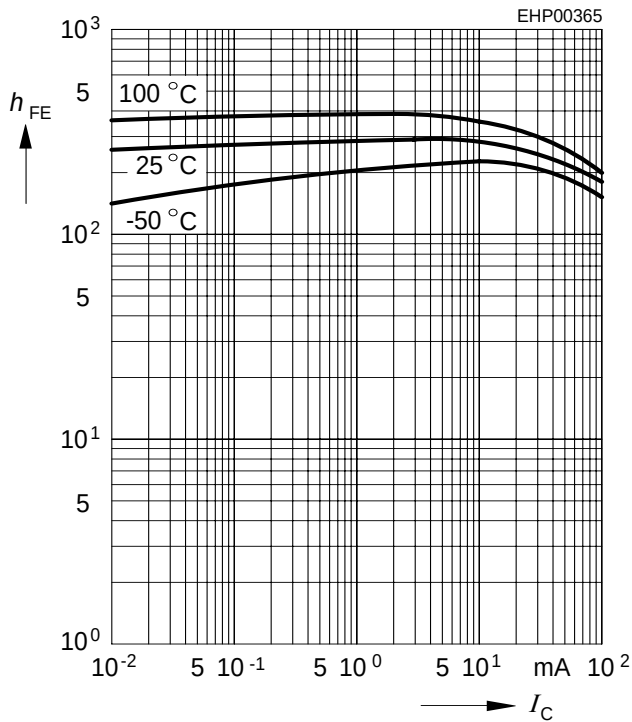
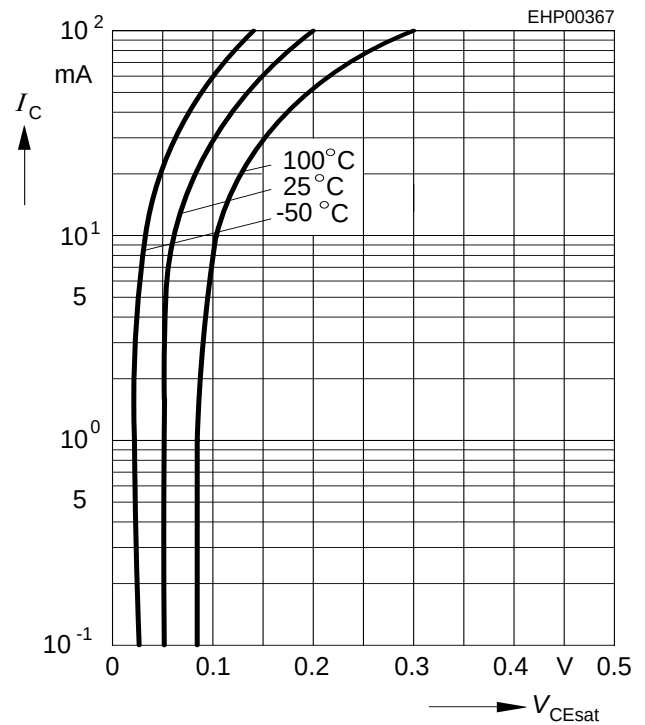
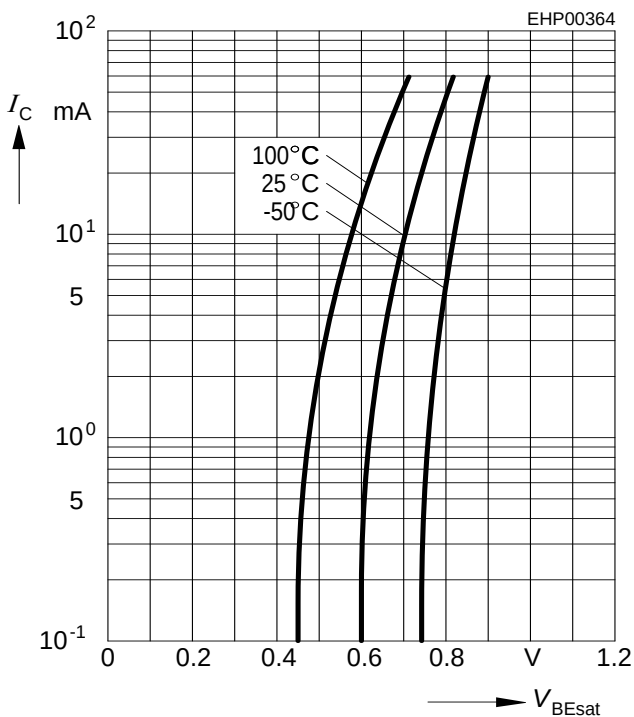
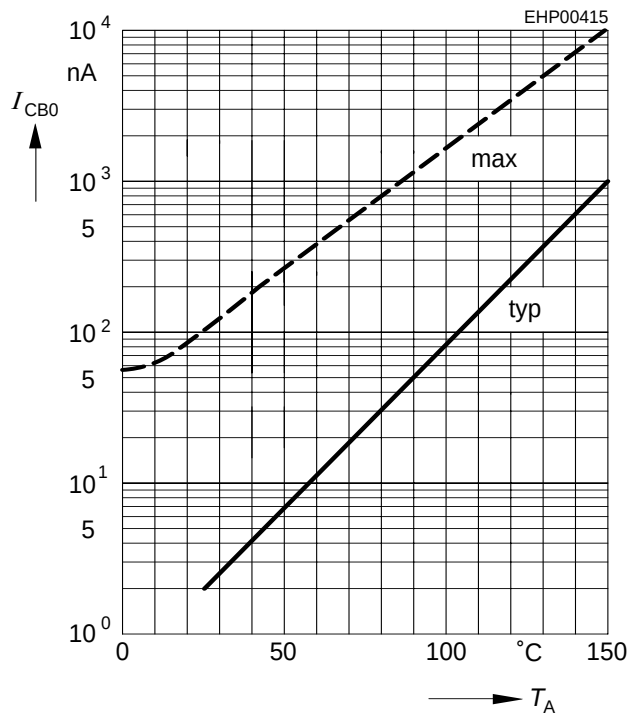
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$, $I_B = 0$, BC847..., BC850... $I_C = 10\text{ mA}$, $I_B = 0$, BC848..., BC849...	$V_{(BR)CEO}$	45 30	- -	- -	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC847..., BC850... $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC848..., BC849...	$V_{(BR)CBO}$	50 30	- -	- -	
Emitter-base breakdown voltage $I_E = 0$, $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	-	6	-	
Collector-base cutoff current $V_{CB} = 45\text{ V}$, $I_E = 0$ $V_{CB} = 30\text{ V}$, $I_E = 0$, $T_A = 150\text{ }^\circ\text{C}$	I_{CBO}	- -	0.015 5	- -	μA
DC current gain ¹⁾ $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, $h_{FE}\text{-grp.A}$ $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, $h_{FE}\text{-grp.B}$ $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, $h_{FE}\text{-grp.C}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $h_{FE}\text{-grp.C}$	h_{FE}	- - - 110 200 420	140 250 480 180 290 520	- - - 220 450 800	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}	- -	90 200	250 600	mV
Base emitter saturation voltage ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{BEsat}	- -	700 900	- -	
Base-emitter voltage ¹⁾ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	580 -	660 -	700 770	

¹⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

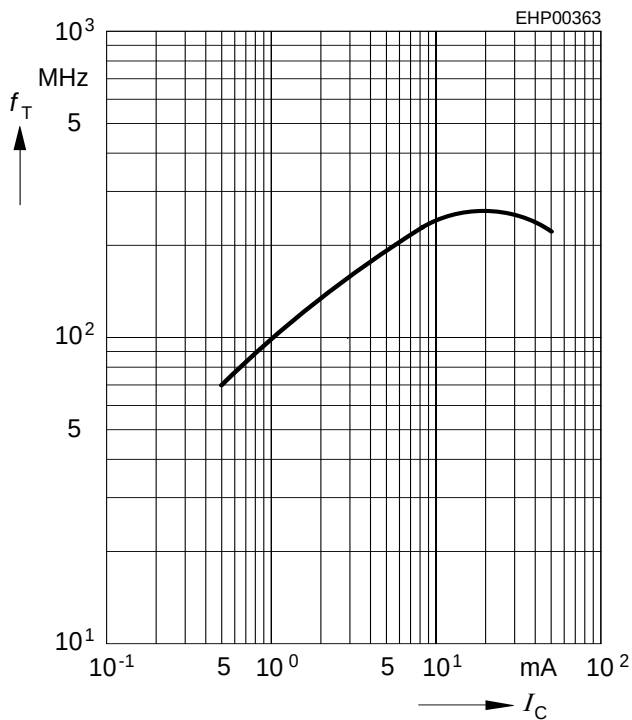
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$	f_T	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	0.95	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	9	-	
Short-circuit input impedance $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.C}$	h_{11e}	- - -	2.7 4.5 8.7	- - -	kΩ
Open-circuit reverse voltage transf. ratio $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.C}$	h_{12e}	- - -	1.5 2 3	- - -	
Short-circuit forward current transf. ratio $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.C}$	h_{21e}	- - -	200 330 600	- - -	
Open-circuit output admittance $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $h_{FE}\text{-grp.C}$	h_{22e}	- - -	18 30 60	- - -	
Noise figure $I_C = 200\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $\Delta f = 200\text{ Hz}$, $R_S = 2\text{ k}\Omega$, BC849..., BC850...	F	-	1.2	4	dB
Equivalent noise voltage $I_C = 200\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, $R_S = 2\text{ k}\Omega$, $f = 10 \dots 50\text{ Hz}$, BC850...	V_n	-	-	0.135	μV

DC current gain $h_{FE} = f(I_C)$
 $V_{CE} = 5 \text{ V}$

Collector-emitter saturation voltage
 $I_C = f(V_{CEsat}), h_{FE} = 20$

Base-emitter saturation voltage
 $I_C = f(V_{BEsat}), h_{FE} = 20$

Collector cutoff current $I_{CBO} = f(T_A)$
 $V_{CB} = 30 \text{ V}$


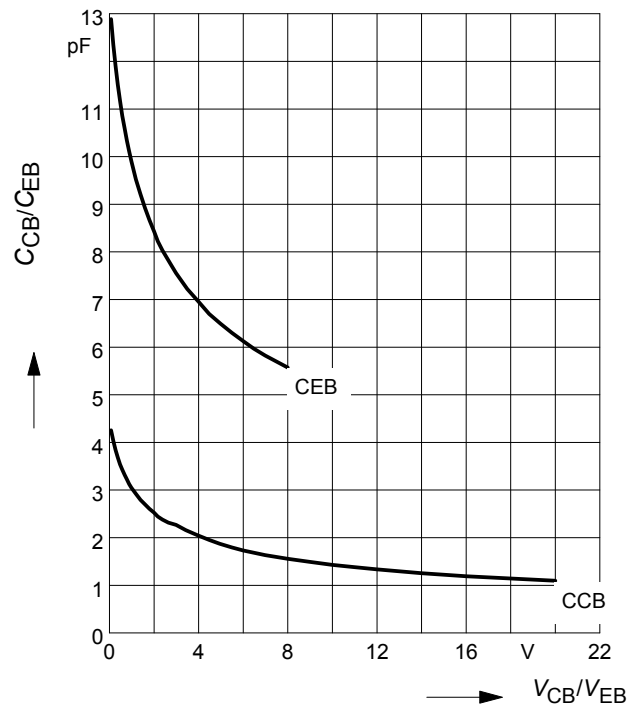
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5 \text{ V}$



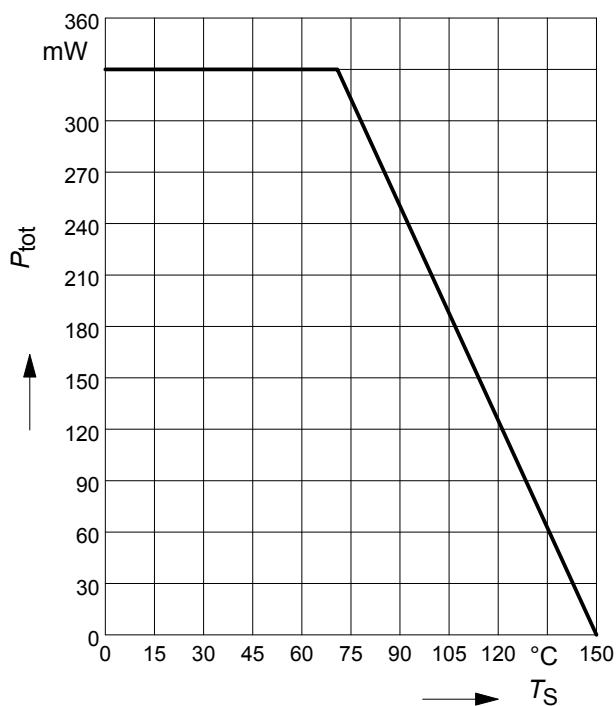
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



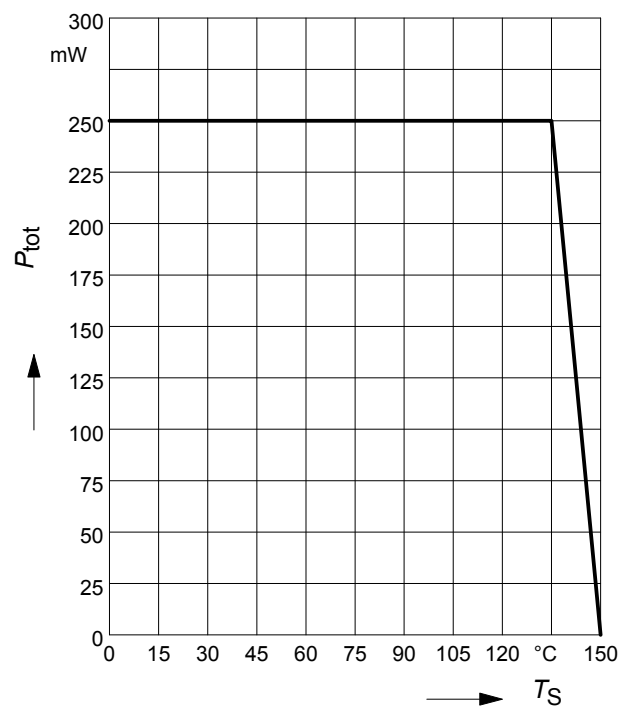
Total power dissipation $P_{tot} = f(T_S)$

BC847-BC850



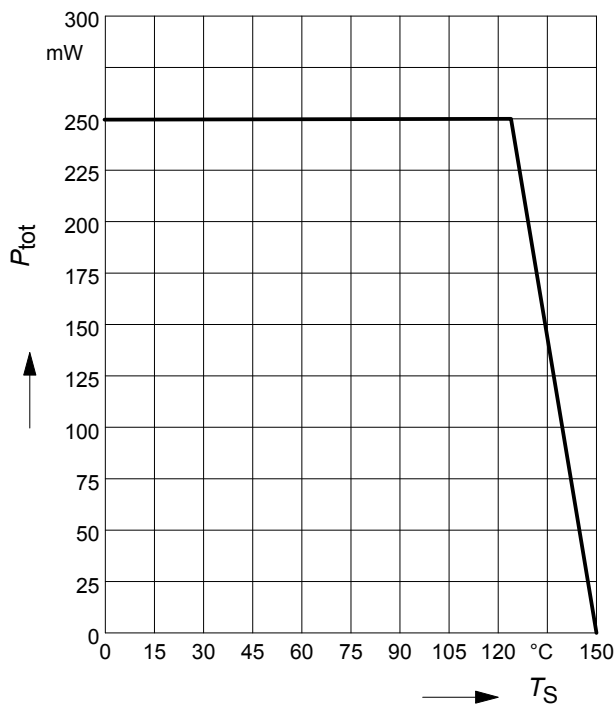
Total power dissipation $P_{tot} = f(T_S)$

BC847BL3/BC848BL3



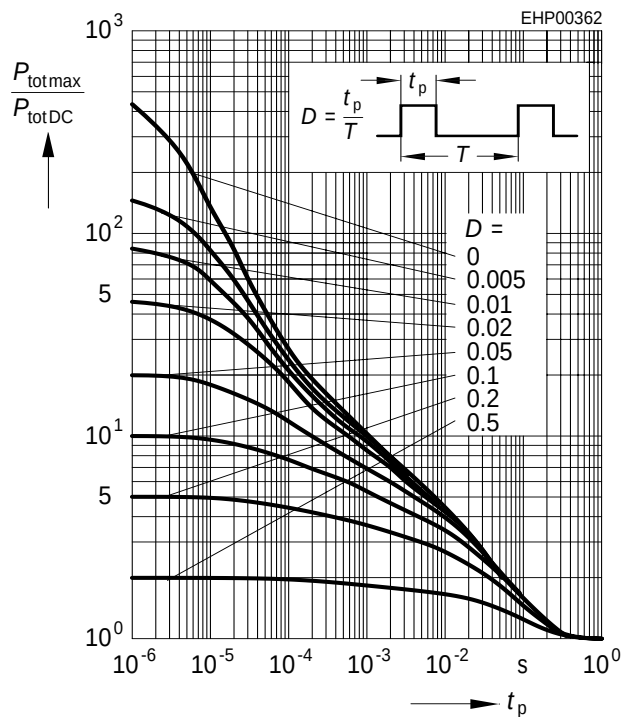
Total power dissipation $P_{\text{tot}} = f(T_S)$

BC847W-BC850W

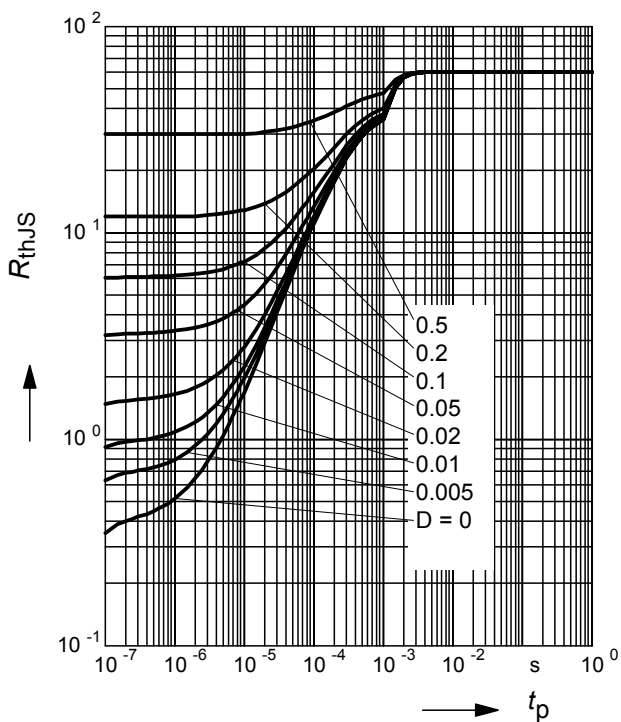

Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BC847/W-BC850/W

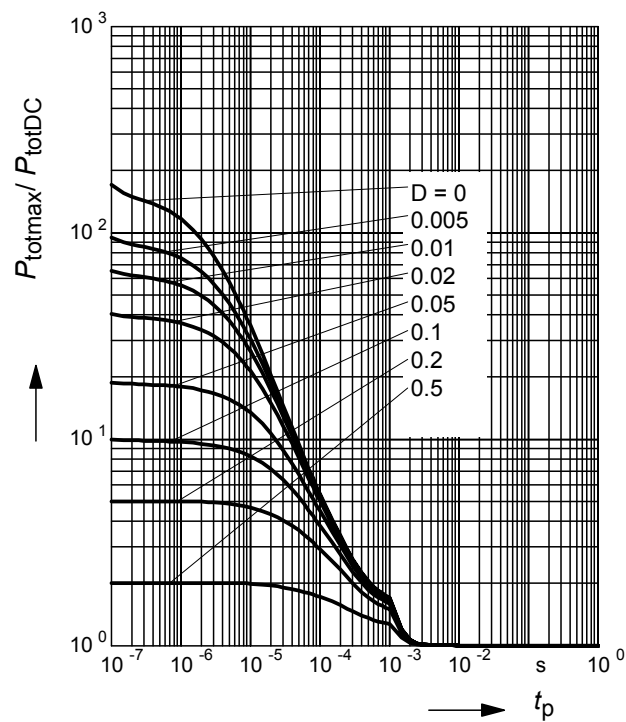

Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

BC847BL3, BC848BL3


Permissible Pulse Load

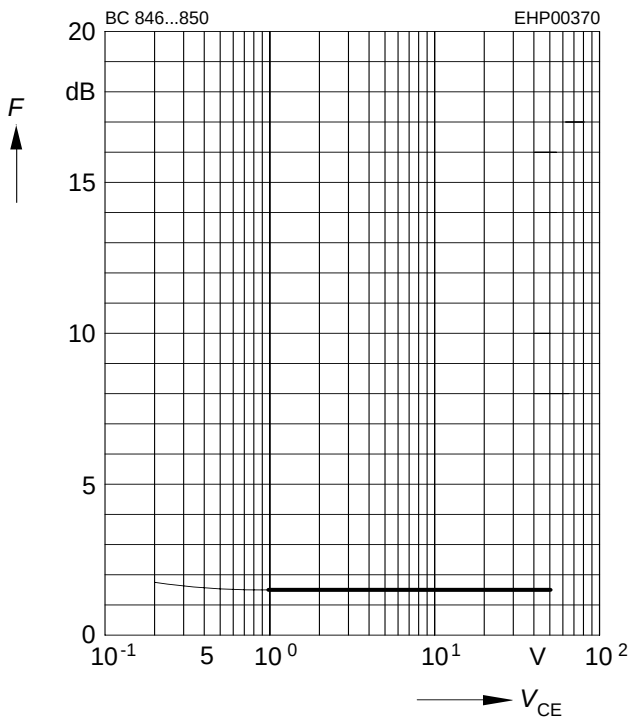
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BC847BL3, BC848BL3



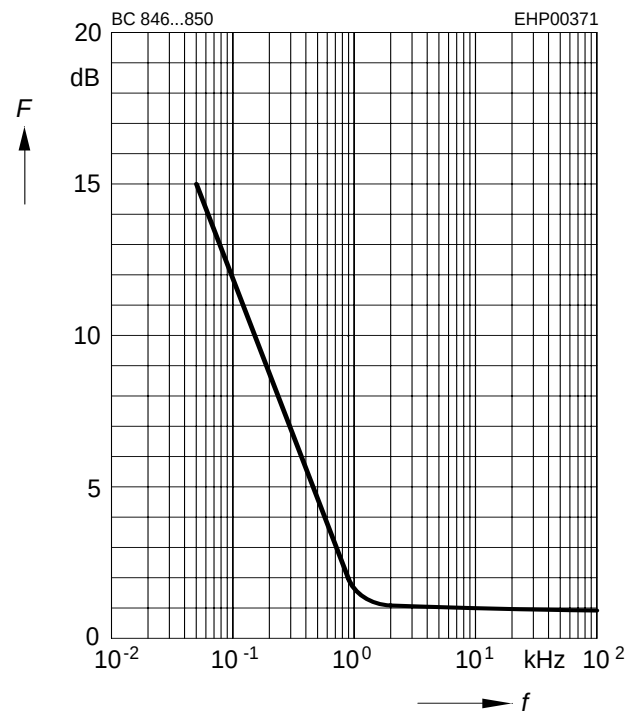
Noise figure $F = f(V_{CE})$

$I_C = 0.2\text{mA}$, $R_S = 2\text{k}\Omega$, $f = 1\text{kHz}$



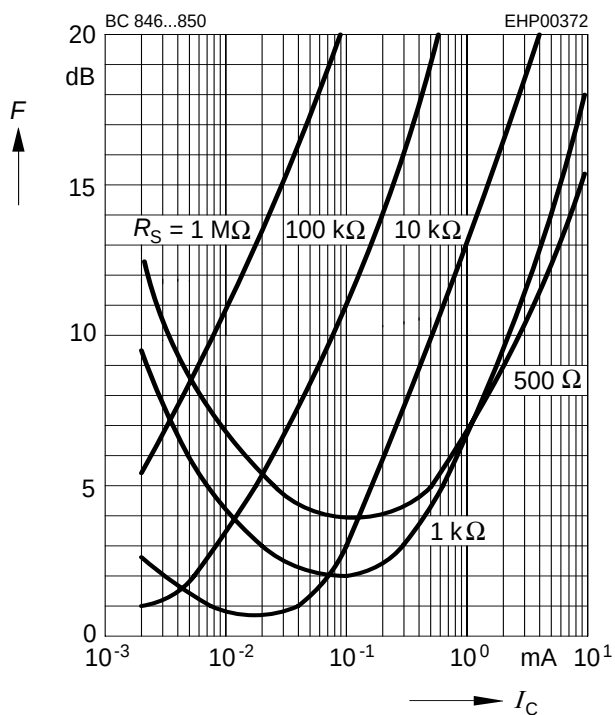
Noise figure $F = f(f)$

$I_C = 0.2\text{ mA}$, $V_{CE} = 5\text{V}$, $R_S = 2\text{ k}\Omega$



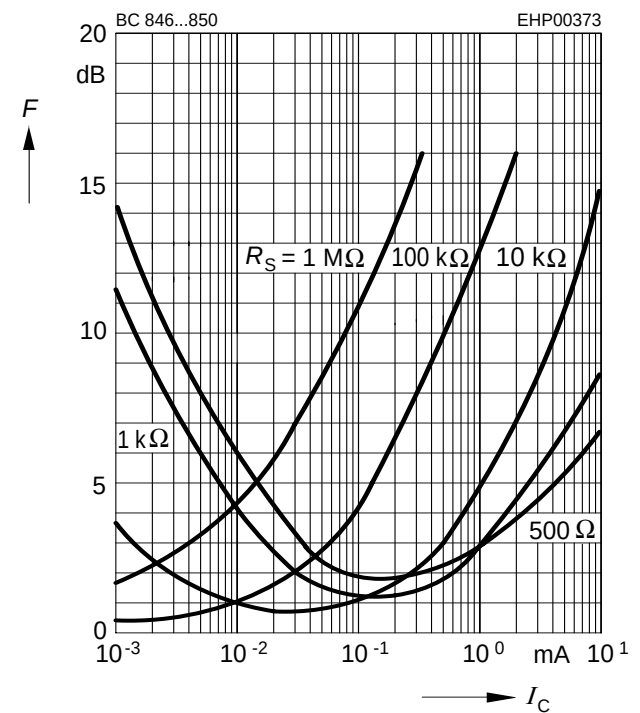
Noise figure $F = f(I_C)$

$V_{CE} = 5\text{V}$, $f = 120\text{Hz}$



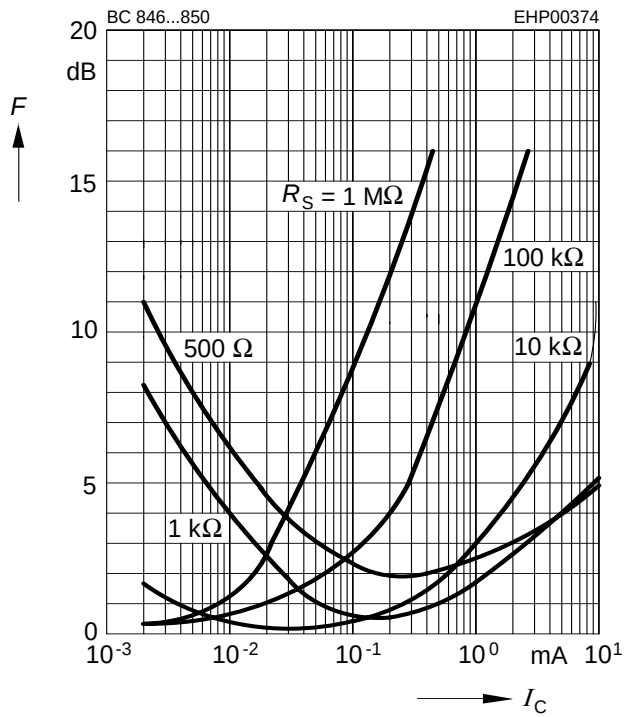
Noise figure $F = f(I_C)$

$V_{CE} = 5\text{V}$, $f = 1\text{kHz}$



Noise figure $F = f(I_C)$

$V_{CE} = 5V, f = 10kHz$

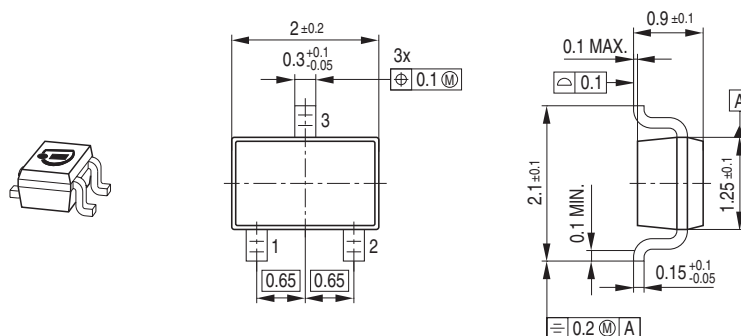


Technical drawing of a shaft with a keyway. The drawing shows the shaft profile with a keyway. Dimensions and tolerances are indicated:

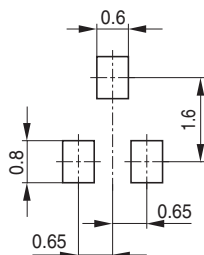
- Overall length: 2.4 ± 0.15
- Keyway depth: 0.15 MIN.
- Keyway width: 1 ± 0.1
- Keyway height: 0.1 MAX.
- Keyway angle: 10° MAX.
- Keyway radius: $0.08 \dots 0.15$
- Keyway chamfer: $0 \dots 8^\circ$
- Keyway position: 1 ± 0.1
- Keyway feature: $\boxed{A}$
- Surface texture: $\sqrt{0.2} \text{ (M) A}$

The diagram shows a top-down view of a BCW66 LED package. It is a rectangular component with four pins. The top pin is labeled 'Pin 1'. The package has a central rectangular area containing the text 'EH S' and a date code '05 05'. To the right of the package, the Infineon logo is shown with the text 'Manufacturer' below it. Below the logo, the date code '2005, June' is shown with 'Date code (YM)' below it. At the bottom right, the text 'BCW66' is shown with 'Type code' below it.

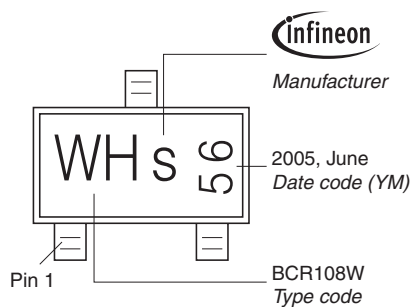
Package Outline



Foot Print

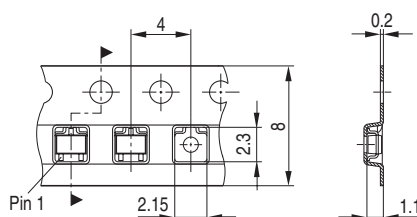


Marking Layout (Example)

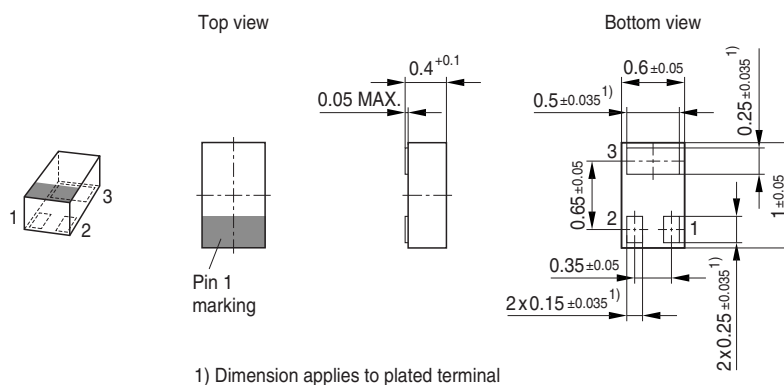


Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 10.000 Pieces/Reel

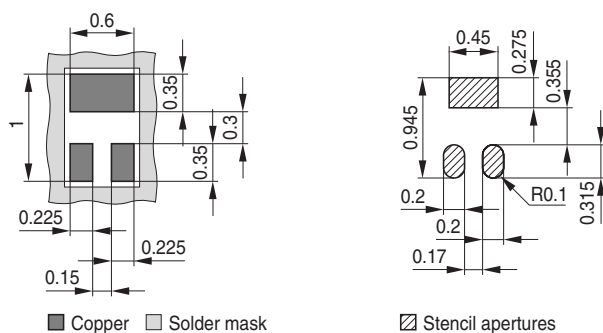


Package Outline

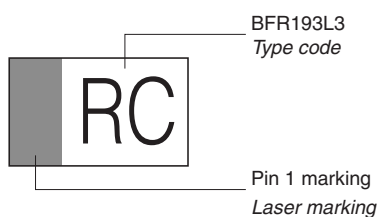


Foot Print

For board assembly information please refer to Infineon website "Packages"

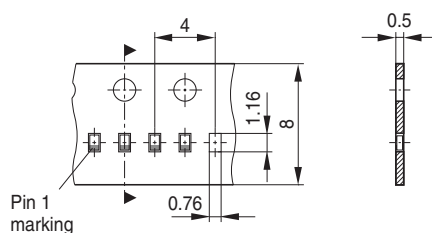


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel



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